#### SILICON (Si) POWER MOSFET A CEZ6R40SL



# CEZ6R40SL

## 65V A 3.6mΩ A 93A A Si MOSFET

SILICON SI MOSFET A SMD type

MGT **A** Manufacturer Group of Technology

N-channel enhancement mode UL94V-0 rated flame retardant epoxy PPAK5x6 package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability

## **MAXIMUM RATINGS**

Parameter ( $T_A = 25^{\circ}C$ , unless otherwise noted)		Characteristics
Drain-Source Voltage	V <sub>DS</sub>	65V
Gate-Source Voltage	V <sub>GS</sub>	±20V
Continuous Drain Current at R <sub>TH_JC</sub>	Ι <sub>D</sub>	93A
Continuous Drain Current at R <sub>TH_JA</sub>	Ι <sub>D</sub>	27A
Pulsed Drain Current at R <sub>TH_JC</sub> Note 1	I <sub>DM</sub>	372A
Pulsed Drain Current at R <sub>TH_JA</sub> Note 1	I <sub>DM</sub>	108A
Maximum Power Dissipation	PD	73W
Single Pulsed Avalanche Energy Note 5	E <sub>AS</sub>	250mJ
Single Pulsed Avalanche Current Note 5	I <sub>AS</sub>	10A
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

#### **THERMAL CHARACTERISTICS**

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R <sub>TH_JC</sub>	1.7°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>TH_JA</sub>	20°C/W

#### **APPLICATIONS**

Audio	Battery Management	DC/DC	Industrial	Power
Amplifier	Systems	Converter	Control	Switches
<b>(</b> )	+ 4 -			

#### **PIN DESCRIPTION**

Circuit Diagram	Outline - Bottom View	Pin No.	Description
G (4) S (1,2,3)		1 2 3 4 5	Source Source Source Gate Drain

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RoHS

REACH

FREE



## **ELECTRICAL CHARACTERISTICS A T**<sub>A</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = 250\mu A$	BV <sub>DSS</sub>	65			V
Zero Gate Voltage Drain Current	$V_{DS} = 65V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 20V$ , $V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS}$ = -20V, $V_{DS}$ = 0V	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	V <sub>GS(th)</sub>	1		3	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_{D} = 20A$	R <sub>DS(ON)</sub>		3.6	4.5	mΩ
Static Drain-Source On-Resistance	$V_{GS}$ = 4.5V, $I_{D}$ = 15A	R <sub>DS(ON)</sub>		5.7	7.4	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS}$ = 30V, $V_{GS}$ = 0V, f = 1MHz	C <sub>ISS</sub>		1790		рF
Output Capacitance	$V_{DS} = 30V, V_{GS} = 0V, f = 1MHz$	Coss		725		рF
Reverse Transfer Capacitance	$V_{DS}$ = 30V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		15		рF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{DD}$ = 30V, $V_{GS}$ = 10V, $I_D$ = 20A, $R_{G(ext)}$ = 25 $\Omega$	t <sub>D(ON)</sub>		22		ns
Turn-On Rise Time	$V_{\text{DD}}$ = 30V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 20A, $R_{\text{G(ext)}}$ = 25 $\Omega$	t <sub>R</sub>		28		ns
Turn-Off Delay Time	$V_{\text{DD}}$ = 30V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 20A, $R_{\text{G(ext)}}$ = 25 $\Omega$	t <sub>D(OFF)</sub>		143		ns
Turn-Off Fall Time	$V_{\text{DD}}$ = 30V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 20A, $R_{\text{G(ext)}}$ = 25 $\Omega$	t <sub>F</sub>		90		ns
Total Gate Charge	$V_{DS} = 30V, V_{GS} = 4.5V, I_D = 20A$	Q <sub>G</sub>		26		nC
Gate Source Charge	$V_{DS} = 30V, V_{GS} = 4.5V, I_D = 20A$	Q <sub>GS</sub>		4		nC
Gate Drain Charge	$V_{DS}$ = 30V, $V_{GS}$ = 4.5V, $I_{D}$ = 20A	$\mathbf{Q}_{GD}$		15		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current <sup>Note3</sup>		I <sub>S</sub>			60	A
Drain-Source Diode Forward Voltage <sup>Note3</sup>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A	$V_{\text{SD}}$			1.2	V

#### Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board,  $t \le 10$  sec

3: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4: Guaranteed by design, not subject to production testing.

5: L = 5mH,  $I_{AS}$  = 10A,  $V_{DD}$  = 24V,  $R_{G}$  = 25 $\Omega$ , Starting  $T_{J}$  = 25 $^{\circ}$ C

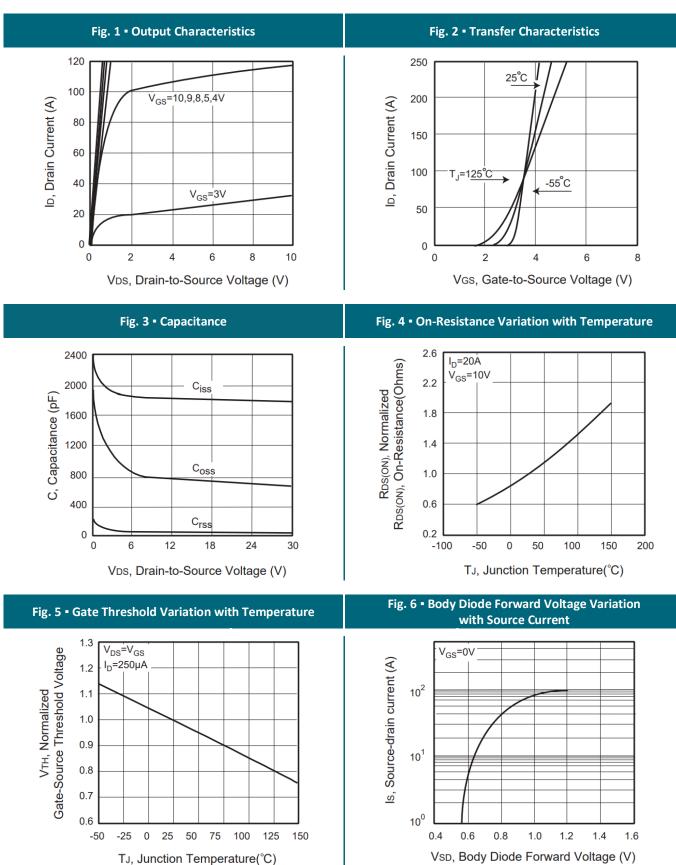
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CET MOS

## **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**



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#### **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**

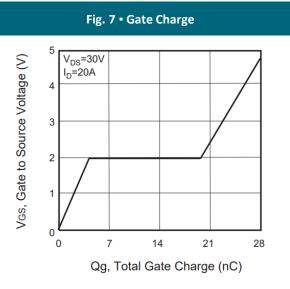


Fig. 9 - Breakdown Voltage Variation vs. Temperature

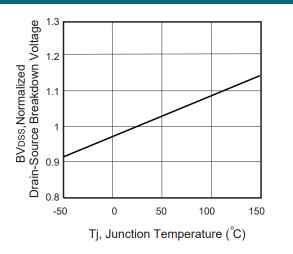
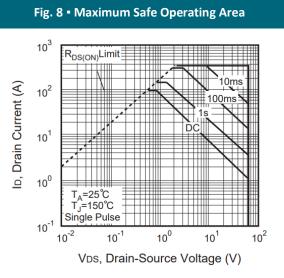
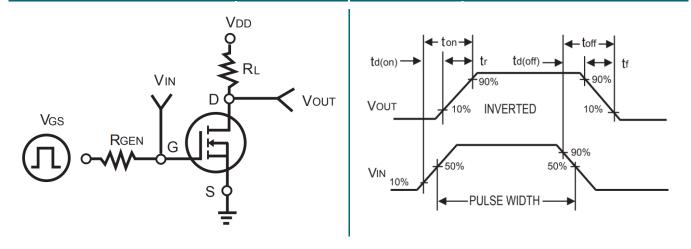


Fig. 10 - Switching Test Circuit





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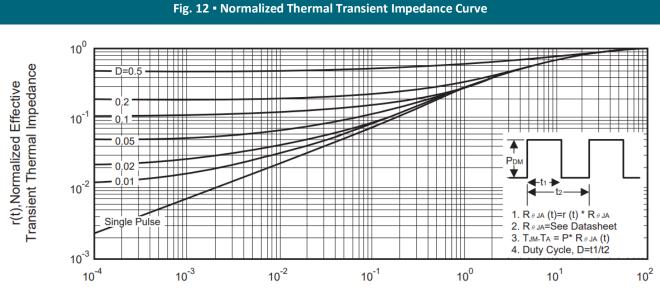


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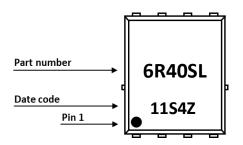


## **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**



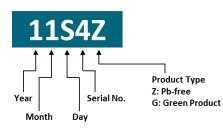
Square Wave Pulse Duration (sec)

#### PART MARKING



## DATE CODE

Example: 11S4Z



Coding list for "Day"									
1	2	3	4	5	6	7	8	9	Α
01	02	03	04	05	06	07	08	09	10
В	С	D	Ε	F	G	Н		J	K
11	12	13	14	15	16	17	18	19	20
L	Μ	Ν	0	Ρ	Q	R	S	Т	U
21	22	23	24	25	26	27	28	29	30
V									
31									

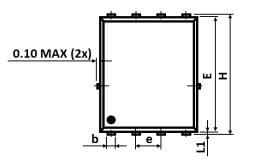
Coding list for "Month"

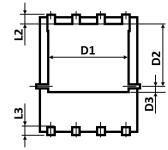


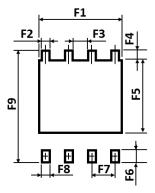
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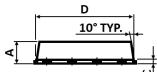


## PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	0.800	-	1.170	E	5.650	-	5.900
b	0.340	-	0.490	е		1.270 TYP	
с	0.200	-	0.340	Н	5.900	-	6.150
D	4.800	-	5.100	L1	0.050	-	0.250
D1	3.800	-	4.200	L2	0.380	-	0.620
D2	3.180	-	3.780	L3	0.380	-	0.750
D3	0.150	-	0.360				

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	4.500	-	F6	-	0.800	-
F2	-	0.500	-	F7	-	1.270	-
F3	-	0.770	-	F8	-	0.500	-
F4	-	0.550	-	F9	-	6.250	-
F5	_	3.650	-				

Notes: 1. The suggested land pattern dimensions have been provided for reference only. 2. For further information, please reference document IPC-7351A.

# **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.	
CEZ6R40SL	PPAK 5x6	Reel	2,500pcs	5,000pcs	40,000pcs	

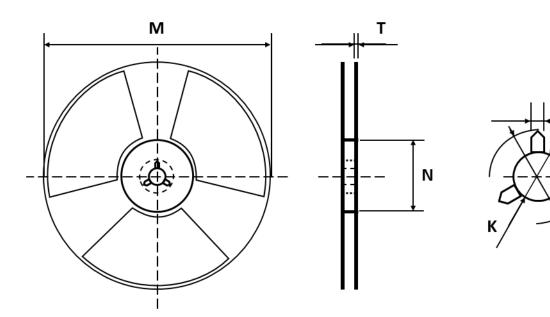


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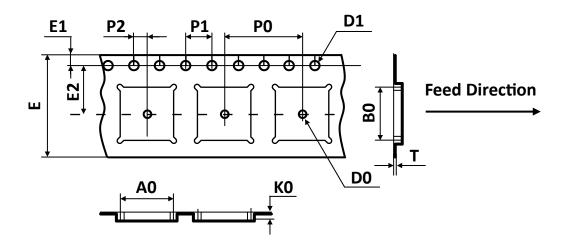


#### **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	N	т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
12mm	Ø330	±2.00	±1.00	±0.20	±0.50	+0.50 -0.20	±0.50

# TAPE DIMENSIONS All dimensions in mm



Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
	6.50	5.28	2.00	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
PPAK 5x6	±0.10	±0.10	±0.10	±0.25	±0.10	+0.30 -0.10	±0.10	±0.05	±0.10	±0.10	±0.05	±0.02

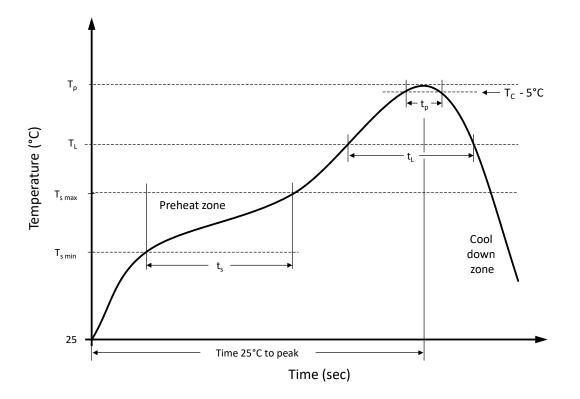


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#### **RECOMMENDED REFLOW SOLDERING PROFILE**



#### **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	tL	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes

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#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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